

MITSUBISHI HIGH SPEED CMOS

M74HC266AP/FP/DP

6249827 MITSUBISHI (DGTL LOGIC)

91D 13222 D

QUADRUPLE 2-INPUT EXCLUSIVE NOR GATE WITH OPEN-DRAIN OUTPUTS

T-43-21

DESCRIPTION

The M74HC266A is a semiconductor integrated circuit consisting of four 2-input exclusive NOR gates with open-drain outputs.

FEATURES

- Open drain outputs
- High-speed: 8ns typ. ($C_L=15pF, V_{CC}=5V$)
- Low power dissipation: $5\mu W/\text{package}$, max ($V_{CC}=5V, T_a=25^\circ C$, quiescent state)
- High noise margin: 30% of V_{CC} , min ($V_{CC}=4.5V, 6V$)
- Capable of driving 10 74LSSTTL loads
- Wide operating voltage range: $V_{CC}=2\sim 6V$
- Wide operating temperature range: $T_a=-40\sim +85^\circ C$

APPLICATION

General purpose, for use in industrial and consumer digital equipment.

FUNCTIONAL DESCRIPTION

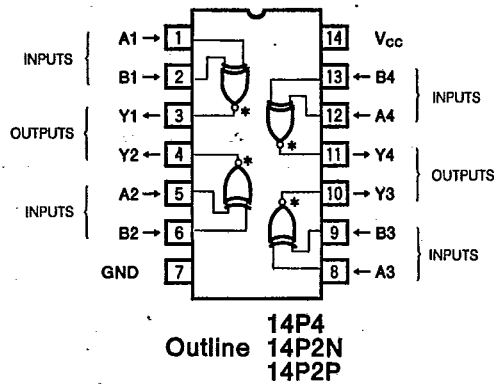
Use of silicon gate technology allows the M74HC266A to maintain the low power dissipation and high noise margin characteristics of the standard CMOS logic 4000B series while giving high-speed performance equivalent to the 74LS266.

Open-drain outputs permit a versatile selection of high output impedances by means of externally connected load resistors. This makes "AND ties" a possibility, unlike the case of normal gates.

When both inputs A and B are either high or low, the output Y will become high, and when the levels of A and B are opposite, the output Y will become low.

Note that, unlike 74LS266, voltages higher than V_{CC} must not be applied to the output.

PIN CONFIGURATION (TOP VIEW)



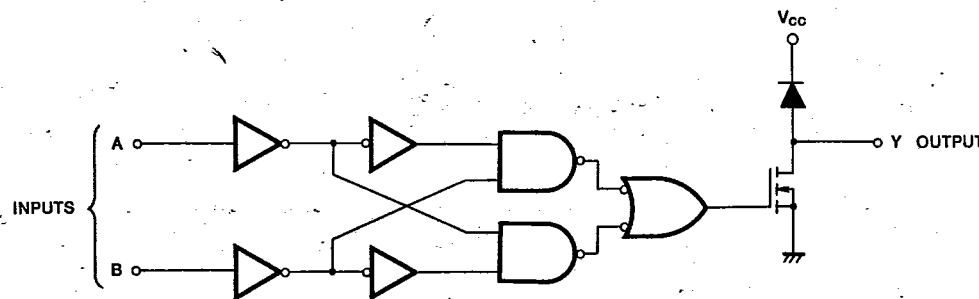
For application requiring normal outputs, another device, the M74HC266 is available with the same functions and pin configuration.

This device of some makers is named 74HC266.

FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	H
H	L	L
L	H	L
H	H	H

LOGIC DIAGRAM (EACH GATE)



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ABSOLUTE MAXIMUM RATINGS ($T_a = -40 \sim +85^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CC}	Supply voltage		$-0.5 \sim +7.0$	V
V_I	Input voltage		$-0.5 \sim V_{CC} + 0.5$	V
V_O	Output voltage		$-0.5 \sim V_{CC} + 0.5$	V
I_{IK}	Input protection diode current	$V_I < 0V$	-20	mA
		$V_I > V_{CC}$	20	
I_{OK}	Output parasitic diode current	$V_O < 0V$	-20	mA
		$V_O > V_{CC}$	20	
I_O	Output current per output pin		25	mA
I_{CC}	Supply/GND current	V_{CC}, GND	± 50	mA
P_d	Power dissipation	(Note 1)	500	mW
T_{stg}	Storage temperature range		$-65 \sim +150$	$^\circ\text{C}$

Note 1 : M74HC266AFP, $T_a = -40 \sim +60^\circ\text{C}$ and $T_a = 60 \sim 85^\circ\text{C}$ are derated at $-6\text{mW}/^\circ\text{C}$.
M74HC266ADP, $T_a = -40 \sim +50^\circ\text{C}$ and $T_a = 50 \sim 85^\circ\text{C}$ are derated at $-5\text{mW}/^\circ\text{C}$.

RECOMMENDED OPERATING CONDITIONS ($T_a = -40 \sim +85^\circ\text{C}$)

Symbol	Parameter	Limits			Unit
		Min	Typ	Max	
V_{CC}	Supply voltage	2		6	V
V_I	Input voltage	0		V_{CC}	V
V_O	Output voltage	0		V_{CC}	V
T_{opr}	Operating temperature range	-40		+85	$^\circ\text{C}$
t_r, t_f	Input risetime, falltime	$V_{CC} = 2.0V$	0	1000	ns
		$V_{CC} = 4.5V$	0	500	
		$V_{CC} = 6.0V$	0	400	

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits					Unit	
			$V_{CC}(V)$	25 $^\circ\text{C}$			-40 $^\circ\text{C}$ ~ +85 $^\circ\text{C}$		
				Min	Typ	Max	Min		Max
V_{IH}	High-level input voltage	$V_O = 0.1V, V_{CC} = 0.1V$ $ I_O = 20\mu\text{A}$ (Note 3)	2.0					V	
			4.5	1.5			1.5		
			6.0	3.15			3.15		
V_{IL}	Low-level input voltage	$V_O = 0.1V, V_{CC} = 0.1V$ $ I_O = 20\mu\text{A}$ (Note 3)	2.0				0.5	V	
			4.5				1.35		
			6.0				1.8		
V_{OL}	Low-level output voltage	$V_I = V_{IH}, V_{IL}$	$I_{OL} = 20\mu\text{A}$	2.0				0.1	V
			$I_{OL} = 20\mu\text{A}$	4.5				0.1	
			$I_{OL} = 20\mu\text{A}$	6.0				0.1	
			$I_{OL} = 4.0\text{mA}$	4.5				0.26	
			$I_{OL} = 5.2\text{mA}$	6.0				0.26	
I_{IH}	High-level input current	$V_I = 6V$	6.0				0.1	μA	
I_{IL}	Low-level input current	$V_I = 0V$	6.0				-0.1	μA	
I_O	Maximum output leakage current	$V_I = V_{IH}, V_{IL}, V_O = V_{CC}$	6.0				0.5	5.0	μA
		$V_I = V_{IH}, V_{IL}, V_O = GND$	6.0				-0.5	-5.0	
I_{CC}	Quiescent supply current	$V_I = V_{CC}, GND, I_O = 0\mu\text{A}$	6.0				1.0	10.0	μA

SWITCHING CHARACTERISTICS ($V_{CC} = 5V, T_a = 25^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
t_{THL}	High-level to low-level output transition time	$R_L = 1k\Omega$ $C_L = 15pF$ (Note 3)			10	ns
t_{PLH}	Low-level to high-level and high-level to low-level	$R_L = 1k\Omega, C_L = 5pF$ (Note 3)			23	ns
t_{PHL}	output propagation time	$R_L = 1k\Omega, C_L = 15pF$ (Note 3)			17	ns



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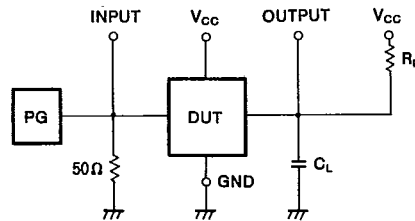
T-43-21

SWITCHING CHARACTERISTICS ($V_{CC} = 2\sim 6V, T_a = -40\sim +85^\circ C$)

Symbol	Parameter	Test conditions	Limits						Unit
			$V_{CC}(V)$	25°C			-40~+85°C		
				Min	Typ	Max	Min	Max	
t_{THL}	High-level to low-level output transition time		2.0			75		95	ns
			4.5			15		19	
			6.0			13		16	
t_{PLH}	Low-level to high-level and high-level to low-level	$R_L = 1k\Omega$ $C_L = 50pF$ (Note 3)	2.0			125		155	ns
			4.5			25		31	
			6.0			23		26	
t_{PHL}	output propagation time		2.0			100		125	ns
			4.5			20		25	
			6.0			17		21	
C_I	Input capacitance						10		pF
C_O	Output capacitance	$A = B = V_{CC}, GND$					10		pF
C_{PD}	Power dissipation capacitance (Note 2)				16				pF

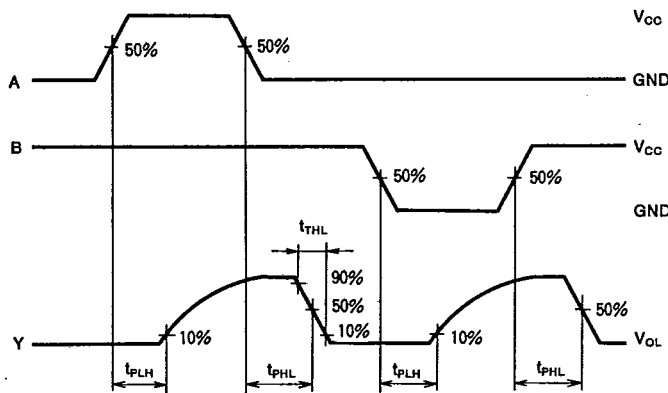
Note 2 : C_{PD} is the internal capacitance of the IC calculated from operation supply current under no-load conditions. (per gate)
The power dissipation during operation under no-load conditions is calculated using the following formula:
 $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_I + I_{CC} \cdot V_{CC}$

Note 3 : Test Circuit



- (1) The pulse generator (PG) has the following characteristics (10%~90%): $t_r = 6ns, t_f = 6ns$
- (2) The capacitance C_L includes stray wiring capacitance and the probe input capacitance.

TIMING DIAGRAM



MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES

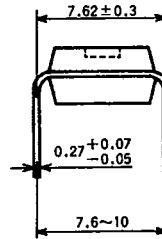
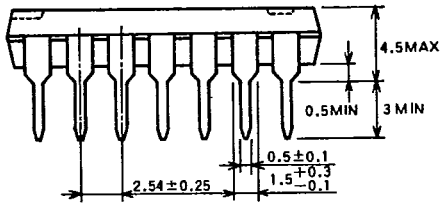
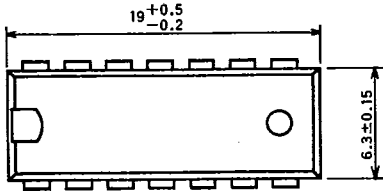
6249827 MITSUBISHI (DGTL LOGIC)

91D 12849

D T-90-20

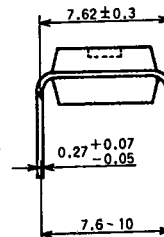
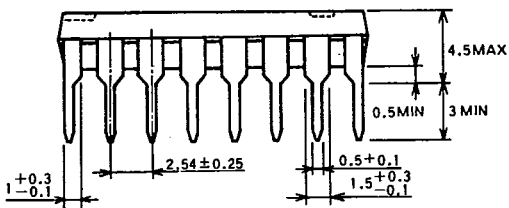
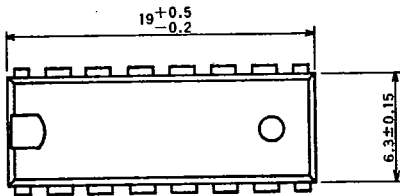
TYPE 14P4 14-PIN MOLDED PLASTIC DIP

Dimension in mm



TYPE 16P4 16-PIN MOLDED PLASTIC DIP

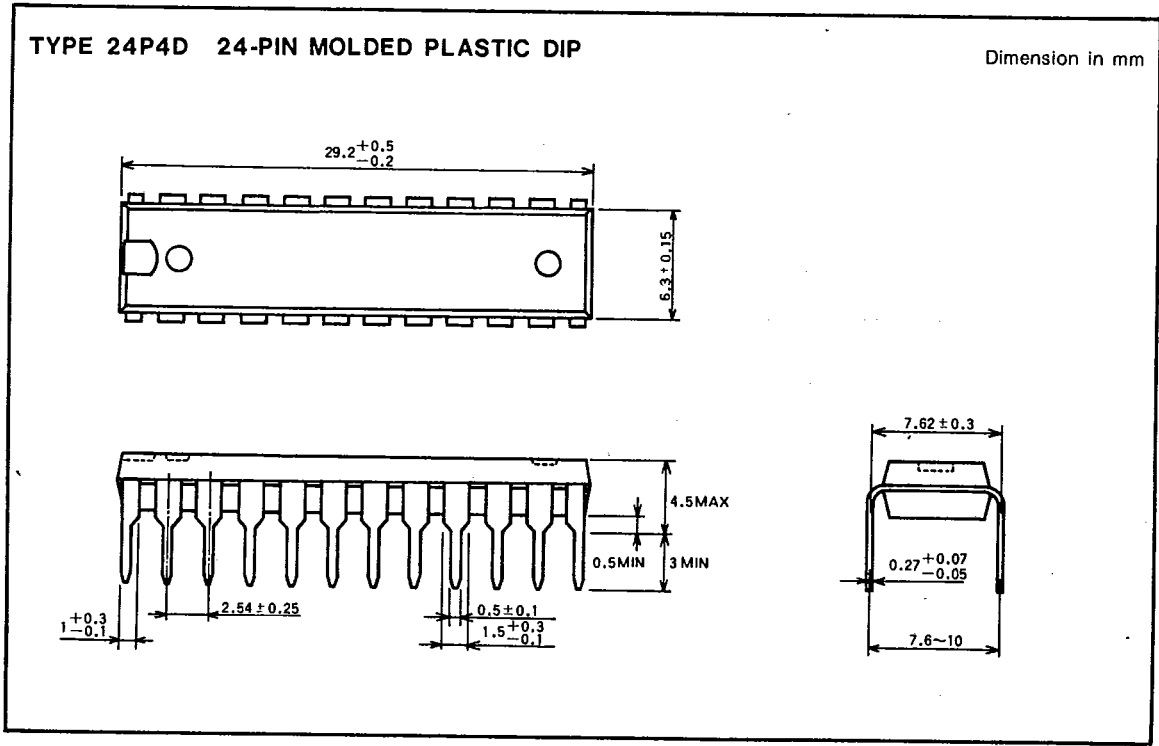
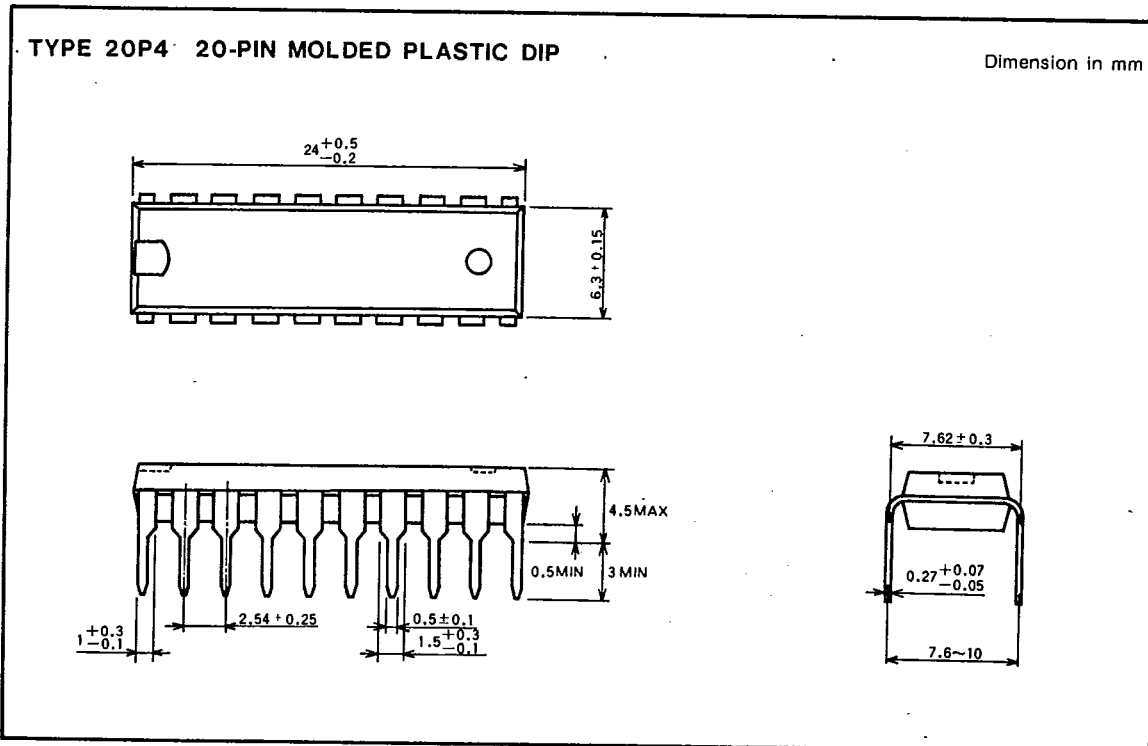
Dimension in mm



MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES

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91D 12850 D.T-90-20



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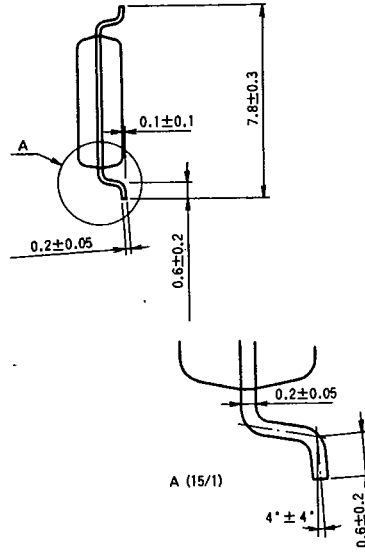
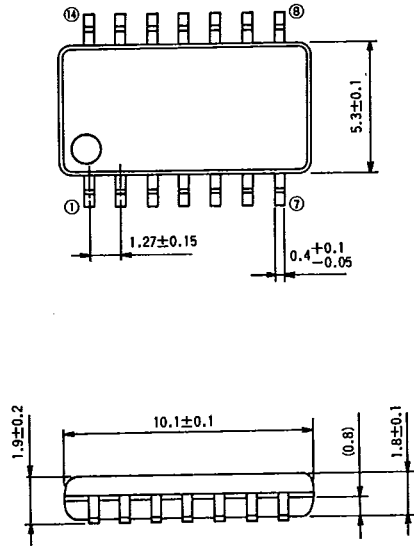
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PACKAGE OUTLINES

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91D 12851 D T-90.20

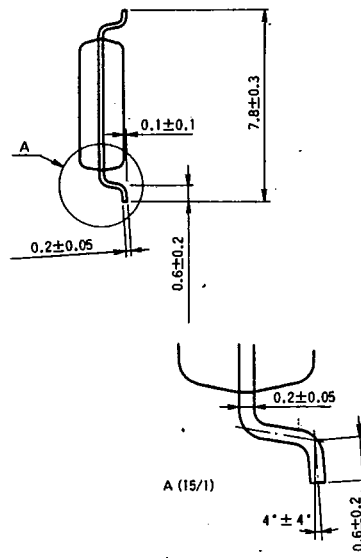
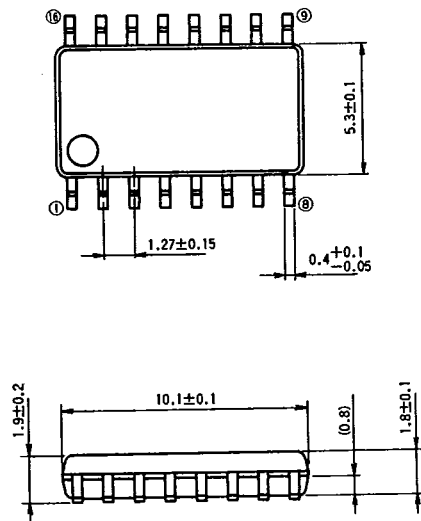
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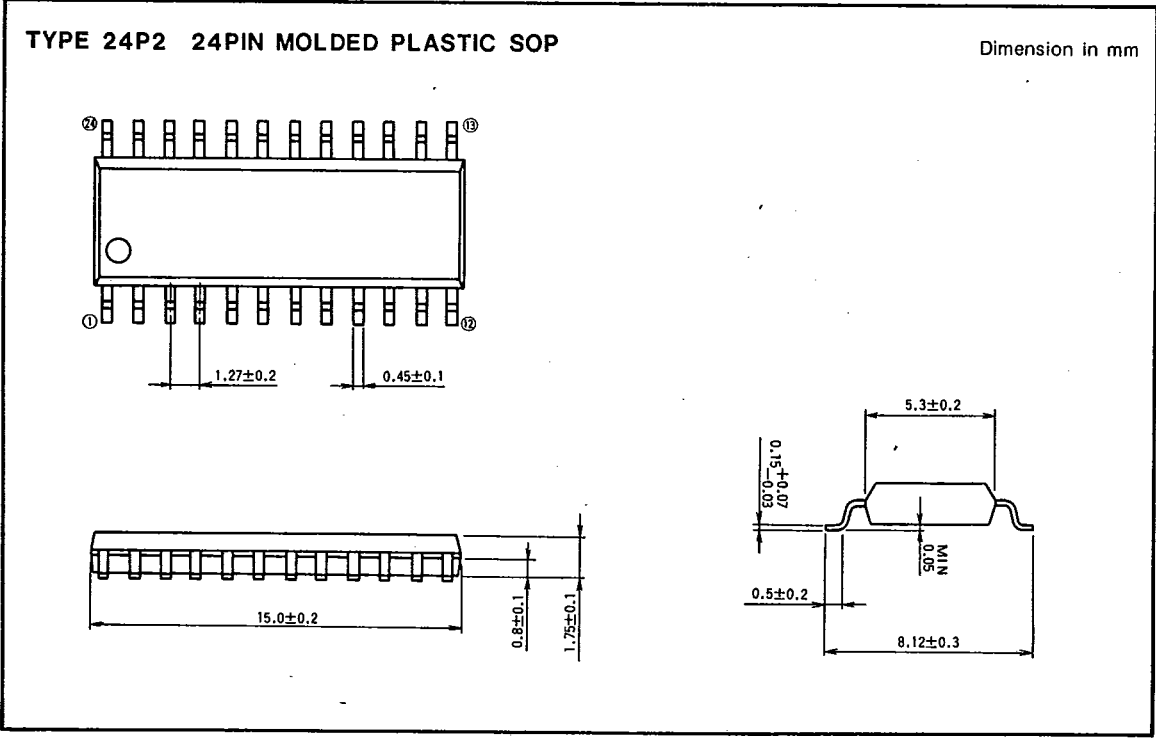
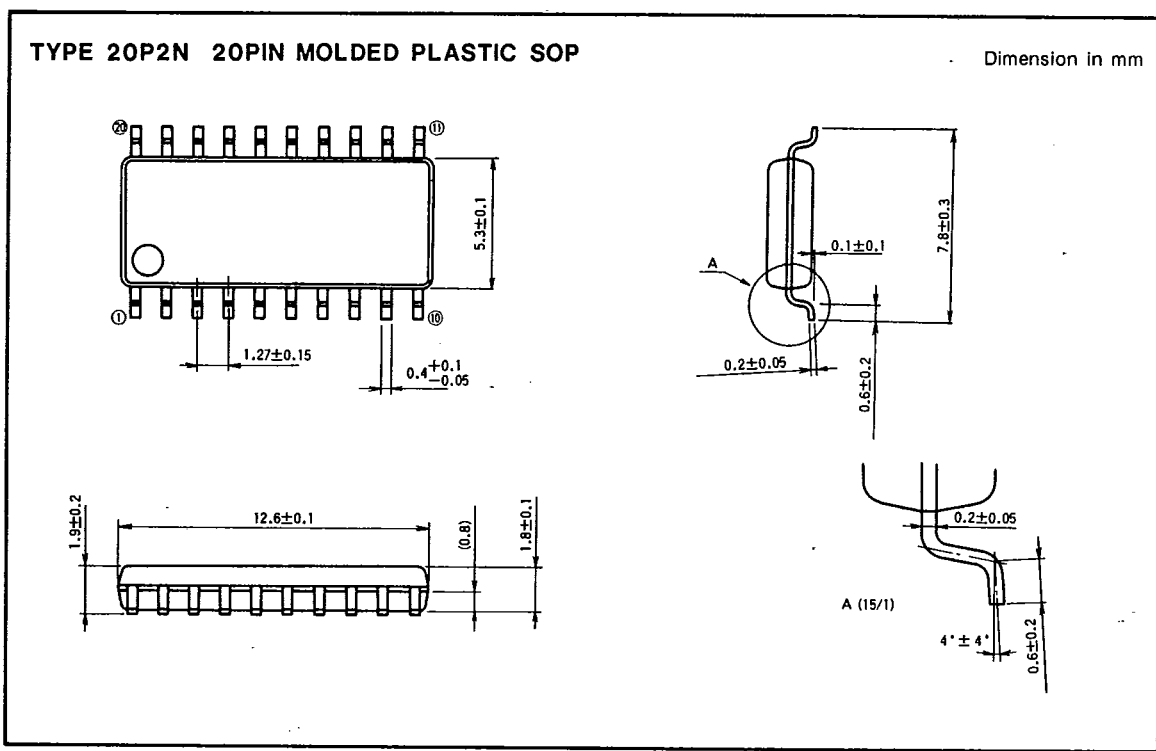
Dimension in mm

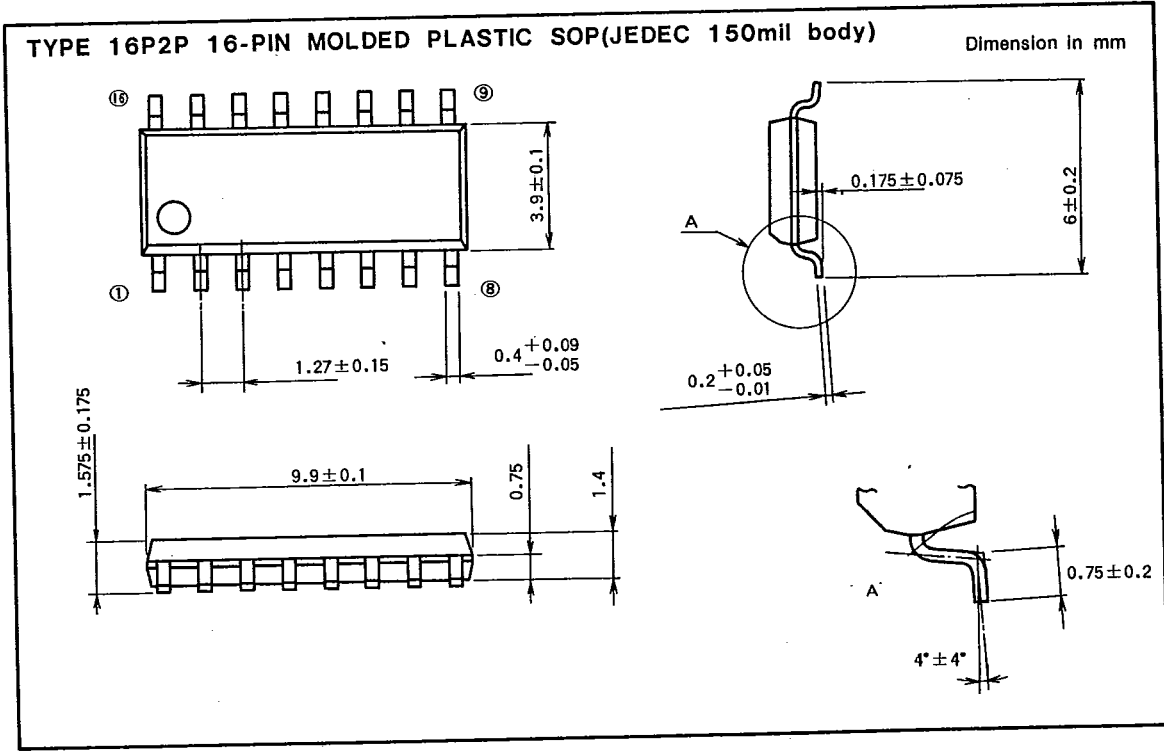
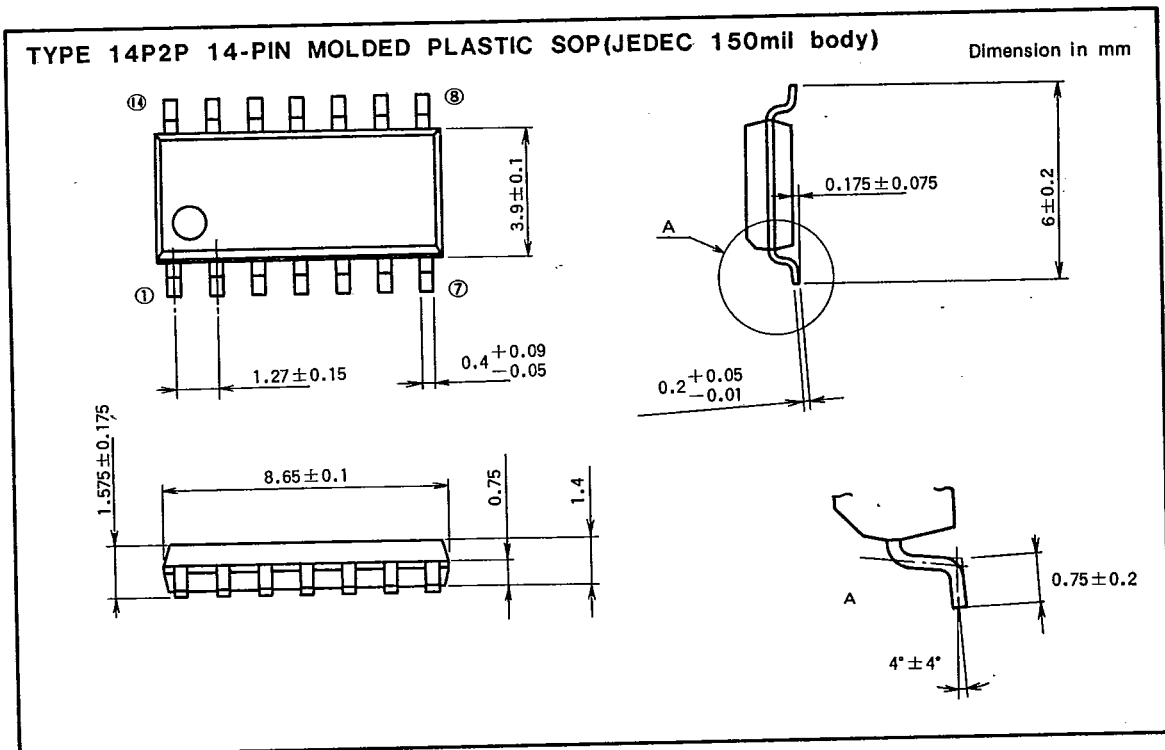


TYPE 16P2N 16PIN MOLDED PLASTIC SOP

Dimension in mm







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PACKAGE OUTLINES

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